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Date: May 2, 2002

Sonia V. McVean

PATENT
36856.599

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Shigeto TAGA U.S. Serial No.: 10/026,811 Filing Date: December 27, 2001 For: SURFACE ACOUSTIC WAVE DEVICE HAVING BUMP ELECTRODES	Art Unit: 2834 Examiner: Unknown
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INFORMATION DISCLOSURE STATEMENT

ASSISTANT COMMISSIONER FOR PATENTS
Washington, D.C. 20231

Dear Sir:

Pursuant to 37 C.F.R. § 1.56, submitted herewith are copies of one (1) reference cited in the enclosed search report issued in a corresponding Japanese patent application. For the Examiner's convenience, we have enclosed an English translation of the Japanese search report and a completed Form PTO-1449. The statement is not a representation that all of the information cited is necessarily effective as prior art against the application.

I hereby state that each item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign

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application not more than 3 months prior to the filing of this statement, and that this is the first citation of these prior art references by a foreign patent office in a counterpart foreign patent application. Accordingly, no fee is necessary for the filing of this statement. Should the Commissioner determine otherwise, the Commissioner is authorized to charge Deposit Account No. 50-1353 for any fee shortages, including the petition fee under 37 C.F.R. § 1.17(p).

Applicant(s) respectfully request(s) that the disclosed reference(s) be made of record in the subject application.

Respectfully submitted,



Attorneys for Applicant(s)

Joseph R. Keating
Registration No. 37,368

Christopher A. Bennett
Registration No. 46,710

KEATING & BENNETT LLP
10400 Eaton Place, Suite 312
Fairfax, VA 22030
(703) 385-5200

US 6064120 A	200000516	Apparatus and method for face-to-face connection of a die face to a substrate with polymer electrodes	257/780
US 5985486 A	199911116	Electrochemical device	429/188
US 5896081 A	19990420	Resistance temperature detector (RTD) formed with a surface-mount-device (SMD) structure	338/22R
US 5777390 A	19980707	Transparent and opaque metal-semiconductor-metal photodetectors	257/749
US 6137184 A	20001024	Flip-chip type semiconductor device having recessed-protruded electrodes in press-fit contact	257/785
US 6028011 A	20000222	Method of forming electric pad of semiconductor device and method of forming solder bump	438/745
US 5991989 A	199911130	Method of manufacture of surface acoustic wave device	29/25.35
US 5844347 A	19981201	Saw device and its manufacturing method	310/313R
US 5699027 A	19971216	Surface acoustic wave devices having a guard layer	333/193
US 5440125 A	19950808	Radiation detector having a pyroelectric ceramic detection element	250/338.1
US 5108950 A	19920428	Method for forming a bump electrode for a semiconductor device	438/614
US 4692653 A	19870908	Acoustic transducers utilizing ZnO thin film	310/334
US 4259607 A	19810331	Quartz crystal vibrator using Ni-Ag or Cr-Ni-Ag electrode layers	310/364
US 3891873 A	19750624	Piezoelectric resonator with multi layer electrodes	310/364
US 5712523 A	19980127	Surface acoustic wave device	310/313R
US 5325012 A	19940628	Bonded type piezoelectric apparatus, method for manufacturing the same and bonded type piezoelectric element	310/364
US 4736128 A	19880405	Surface acoustic wave device	310/313R
US 4477952 A	19841023	Piezoelectric crystal electrodes and method of manufacture	29/25.35
US 3959747 A	19760525	Metalized lithium niobate and method of making	333/149
US 5746930 A	19980505	Method and structure for forming an array of thermal sensors	216/87
US 6277523 B1	20010821	Electrochemical device	429/304
US 5796205 A	19980818	Surface acoustic wave device and method of producing the same	310/313R
US 5355568 A	19941018	Method of making a surface acoustic wave device	29/25.35
JP 07187894 A	19950725	Ferroelectric thin film for substrate material for functional devices - has metal film(s) provided through amorphous layer on major portion of substrate	438/155
US 5643804 A	19970701	Method of manufacturing a hybrid integrated circuit component having a laminated body	257/737
US 5134460 A	19920728	Aluminum bump, reworkable bump, and titanium nitride structure for tab bonding	